# SRAM

# 1 MEG x 1 SRAM

## LOW VOLTAGE



## FEATURES

- All I/O pins are 5V tolerant
- High speed: 15, 17, 20, 25, 35 and 45ns
- High-performance, low-power, CMOS double-metal process
- Single +3.3V ±0.3 power supply
- Easy memory expansion with $\overline{CE}$ option
- All inputs and outputs are TTL-compatible
- Complies to JEDEC low-voltage TTL standards

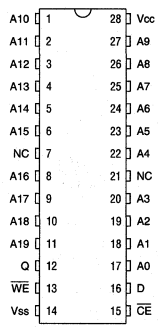
## OPTIONS — MARKING

- Timing
  - 15ns access — -15
  - 17ns access — -17
  - 20ns access — -20
  - 25ns access — -25
  - 35ns access — -35
  - 45ns access — -45
- Packages
  - Plastic DIP (400 mil) — None
  - Plastic SOJ (400 mil) — DJ
  - Plastic SOJ (300 mil) — SJ
- 2V data retention — L
- 2V data retention, low power — LP
- Temperature
  - Commercial (0°C to +70°C) — None
  - Industrial (-40°C to +85°C) — IT
  - Automotive (-40°C to +125°C) — AT
  - Extended (-55°C to +125°C) — XT
- Part Number Example: MT5LC1001DJ-25 L

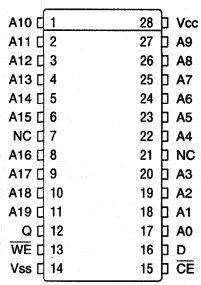
NOTE: Not all combinations of operating temperature, speed, data retention and low power are necessarily available. Please contact the factory for availability of specific part number combinations.

## PIN ASSIGNMENT (Top View)

### 28-Pin DIP (SA-5)




### 28-Pin SOJ (SD-3) (SD-2)




## GENERAL DESCRIPTION

The MT5LC1001 is organized as a 1,048,576 x 1 SRAM using a four-transistor memory cell with a high-speed, low-power CMOS process. Micron SRAMs are fabricated using double-layer metal, double-layer polysilicon technology.

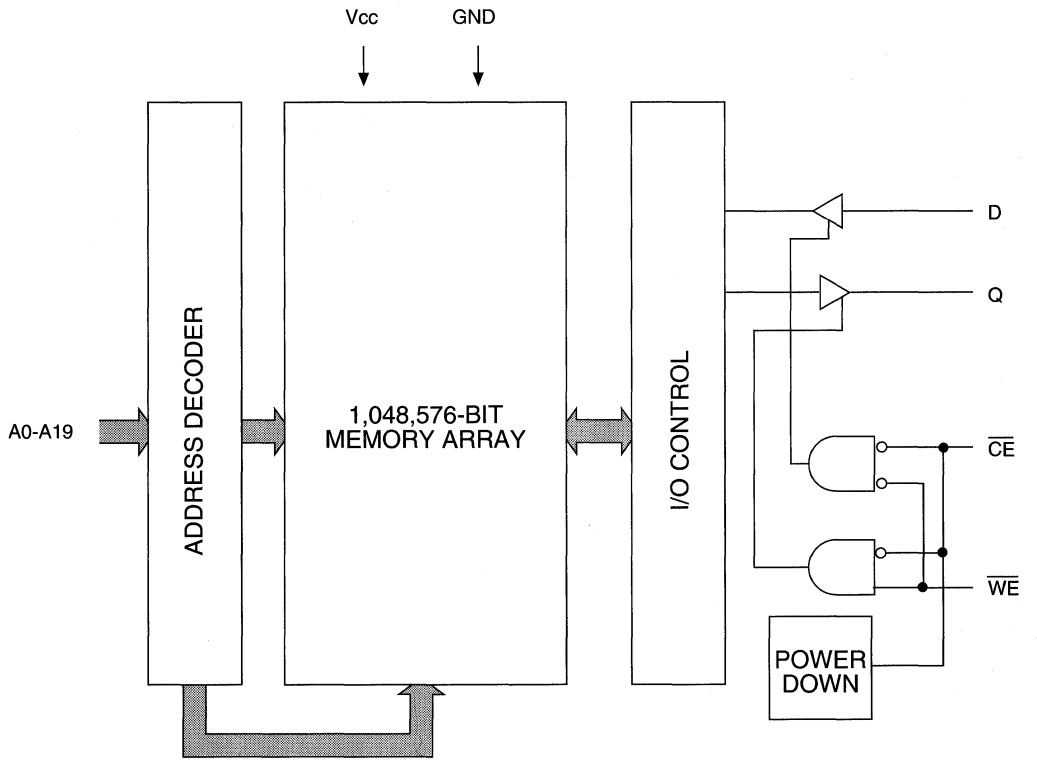
For flexibility in high-speed memory applications, Micron offers chip enable ($\overline{CE}$) capability. This enhancement can place the outputs in High-Z for additional flexibility in system design.

Writing to this device is accomplished when write enable ($\overline{WE}$) and $\overline{CE}$ inputs are both LOW. Reading is accomplished when $\overline{WE}$ remains HIGH while $\overline{CE}$ goes LOW. The device offers a reduced power standby mode when disabled. This allows system designers to meet low standby power requirements.

The "LP" version provides a reduction in both CMOS standby current ($I_{SB2}$) and TTL standby current ($I_{SB1}$) over the standard part. This is achieved through the use of gated inputs on the $\overline{WE}$ and address lines, which also facilitates the design of battery-backed systems. That is, the gated inputs simplify the design effort and circuitry required to protect against inadvertent battery current drain during power-down, when inputs may be at undefined levels.

All devices operate from a single +3.3V power supply and all inputs and outputs are fully TTL-compatible and 5V tolerant. These low-voltage parts are ideal for mixed 3.3V and 5V systems.

## FUNCTIONAL BLOCK DIAGRAM




## TRUTH TABLE

| MODE | $\overline{CE}$ | $\overline{WE}$ | INPUT | OUTPUT | POWER |
|---|---|---|---|---|---|
| STANDBY | H | X | DON'T CARE | HIGH-Z | STANDBY |
| READ | L | H | DON'T CARE | Q | ACTIVE |
| WRITE | L | L | DATA-IN | HIGH-Z | ACTIVE |

## ABSOLUTE MAXIMUM RATINGS*

Voltage on $V_{CC}$ Supply Relative to $V_{SS}$ ..... -0.5V to +4.6V
$V_{IN}$ ..... -0.5V to +6.0V
Storage Temperature (plastic) ..... -55°C to +150°C
Power Dissipation ..... 1W
Short Circuit Output Current ..... 50mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



## ELECTRICAL CHARACTERISTICS AND RECOMMENDED DC OPERATING CONDITIONS

(0°C ≤ $T_A$ ≤ 70°C; Vcc = 3.3V ±0.3V)

| DESCRIPTION | CONDITIONS | SYMBOL | MIN | MAX | UNITS | NOTES |
|---|---|---|---|---|---|---|
| Input High (Logic 1) Voltage | | $V_{IH}$ | 2.0 | 5.5 | V | 1, 2 |
| Input Low (Logic 0) Voltage | | $V_{IL}$ | -0.3 | 0.8 | V | 1, 2 |
| Input Leakage Current | 0V ≤ $V_{IN}$ ≤ Vcc | $I_{LI}$ | -1 | 1 | µA | |
| Output Leakage Current | Output(s) disabled 0V ≤ $V_{OUT}$ ≤ Vcc | $I_{LO}$ | -1 | 1 | µA | |
| Output High Voltage | $I_{OH}$ = -4.0mA | $V_{OH}$ | 2.4 | | V | 1 |
| Output Low Voltage | $I_{OL}$ = 8.0mA | $V_{OL}$ | | 0.4 | V | 1 |
| Supply Voltage | | Vcc | 3.0 | 3.6 | V | 1 |

| | | | | MAX | | | | | | | |
|---|---|---|---|---|---|---|---|---|---|---|---|
| DESCRIPTION | CONDITIONS | SYMBOL | VER | -15 | -17 | -20 | -25 | -35 | -45 | UNITS | NOTES |
| Power Supply Current: Operating | $\overline{CE}$ ≤ $V_{IL}$; Vcc = MAX outputs open f = MAX = 1/tRC | Icc | ALL | 85 | 75 | 65 | 55 | 45 | 40 | mA | 3, 15 |
| Power Supply Current: Standby | $\overline{CE}$ ≥ $V_{IH}$; Vcc = MAX outputs open f = MAX = 1/tRC | $I_{SB1}$ | STD, L | 20 | 18 | 14 | 12 | 8 | 6 | mA | |
| | | | LP | 500 | 500 | 500 | 500 | 500 | 500 | µA | |
| | $\overline{CE}$ ≥ Vcc - 0.2V; Vcc = MAX $V_{IN}$ ≥ Vcc - 0.2V or $V_{IN}$ ≤ $V_{SS}$ + 0.2V | $I_{SB2}$ | STD, L | 300 | 300 | 300 | 300 | 300 | 300 | µA | |
| | | | LP | 100 | 100 | 100 | 100 | 100 | 100 | µA | |

## CAPACITANCE

| DESCRIPTION | CONDITIONS | SYMBOL | MAX | UNITS | NOTES |
|---|---|---|---|---|---|
| Input Capacitance | $T_A$ = 25°C; f = 1 MHz Vcc = 3.3V | $C_I$ | 8 | pF | 4 |
| Output Capacitance | | Co | 8 | pF | 4 |

## ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(Note 5, 13) (0°C ≤ $T_A$ ≤ 70°C; Vcc = 3.3V ±0.3V)

| DESCRIPTION | | -15 | | -17 | | -20 | | -25 | | -35 | | -45 | | | |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| | SYM | MIN | MAX | MIN | MAX | MIN | MAX | MIN | MAX | MIN | MAX | MIN | MAX | UNITS | NOTES |
| **READ Cycle** | | | | | | | | | | | | | | | |
| READ cycle time | $^tRC$ | 15 | | 17 | | 20 | | 25 | | 35 | | 45 | | ns | |
| Address access time | $^tAA$ | | 15 | | 17 | | 20 | | 25 | | 35 | | 45 | ns | |
| Chip Enable access time | $^tACE$ | | 15 | | 17 | | 20 | | 25 | | 35 | | 45 | ns | |
| Output hold from address change | $^tOH$ | 3 | | 3 | | 3 | | 5 | | 5 | | 5 | | ns | |
| Chip Enable to output in Low-Z | $^tLZCE$ | 5 | | 5 | | 3 | | 5 | | 5 | | 5 | | ns | 7 |
| Chip disable to output in High-Z | $^tHZCE$ | | 6 | | 7 | | 8 | | 10 | | 15 | | 18 | ns | 6, 7 |
| Chip Enable to power-up time | $^tPU$ | 0 | | 0 | | 0 | | 0 | | 0 | | 0 | | ns | |
| Chip disable to power-down time | $^tPD$ | | 15 | | 17 | | 20 | | 25 | | 35 | | 45 | ns | |
| **WRITE Cycle** | | | | | | | | | | | | | | | |
| WRITE cycle time | $^tWC$ | 15 | | 17 | | 20 | | 25 | | 35 | | 45 | | ns | |
| Chip Enable to end of write | $^tCW$ | 10 | | 12 | | 12 | | 15 | | 20 | | 25 | | ns | |
| Address valid to end of write | $^tAW$ | 10 | | 12 | | 12 | | 15 | | 20 | | 25 | | ns | |
| Address setup time | $^tAS$ | 0 | | 0 | | 0 | | 0 | | 0 | | 0 | | ns | |
| Address hold from end of write | $^tAH$ | 0 | | 0 | | 0 | | 0 | | 0 | | 0 | | ns | |
| WRITE pulse width | $^tWP$ | 9 | | 12 | | 12 | | 15 | | 20 | | 25 | | ns | |
| Data setup time | $^tDS$ | 7 | | 8 | | 8 | | 10 | | 15 | | 20 | | ns | |
| Data hold time | $^tDH$ | 0 | | 0 | | 0 | | 0 | | 0 | | 0 | | ns | |
| Write disable to output in Low-Z | $^tLZWE$ | 3 | | 3 | | 3 | | 5 | | 5 | | 5 | | ns | 7 |
| Write Enable to output in High-Z | $^tHZWE$ | | 6 | | 7 | | 8 | | 10 | | 15 | | 18 | ns | 6, 7 |

## AC TEST CONDITIONS

| | |
|---|---|
| Input pulse levels | Vss to 3.0V |
| Input rise and fall times | 3ns |
| Input timing reference levels | 1.5V |
| Output reference levels | 1.5V |
| Output load | See Figures 1 and 2 |

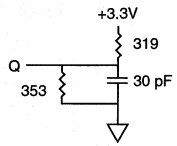



Fig. 1 OUTPUT LOAD EQUIVALENT

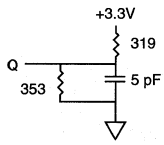



Fig. 2 OUTPUT LOAD EQUIVALENT



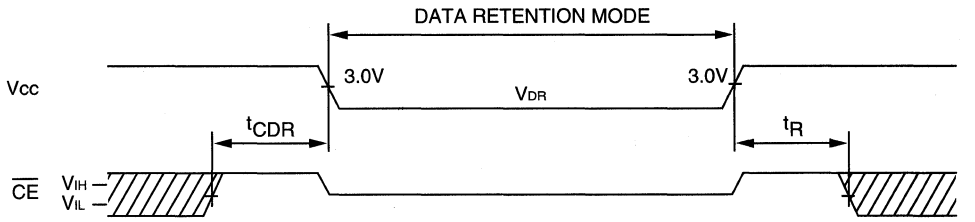
## NOTES

1. All voltages referenced to $V_{SS}$ (GND).
2. Overshoot: $V_{IH} \leq +6.0V$ for $t \leq {}^tRC/2$
   Undershoot: $V_{IL} \geq -2.0V$ for $t \leq {}^tRC/2$
   Power-up: $V_{IH} \leq +6.0V$ and $V_{CC} \leq 3.1V$ for $t \leq 200msec$.
3. $I_{CC}$ is dependent on output loading and cycle rates.
4. This parameter is sampled.
5. Test conditions as specified with the output loading as shown in Fig. 1 unless otherwise noted.
6. ${}^tHZCE$ and ${}^tHZWE$ are specified with CL = 5pF as in Fig. 2. Transition is measured ±200mV from steady state voltage.
7. At any given temperature and voltage condition, ${}^tHZCE$ is less than ${}^tLZCE$, and ${}^tHZWE$ is less than ${}^tLZWE$.
8. $\overline{WE}$ is HIGH for READ cycle.
9. Device is continuously selected. All chip enables and output enables are held in their active state.
10. Address valid prior to, or coincident with, latest occurring chip enable.
11. ${}^tRC$ = Read Cycle Time.
12. Chip enable and write enable can initiate and terminate a WRITE cycle.
13. Contact Micron for IT/AT/XT timing and current specifications; they may differ from the commercial temperature range specifications shown in this data sheet.
14. Typical values are measured at 3.3V, 25°C and 25ns cycle time.
15. Typical currents are measured at 25°C.

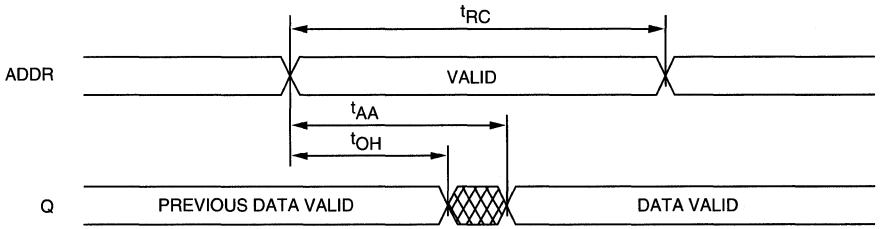
## DATA RETENTION ELECTRICAL CHARACTERISTICS (L and LP versions only)

| DESCRIPTION | CONDITIONS | SYMBOL | MIN | TYP | MAX | UNITS | NOTES |
|---|---|---|---|---|---|---|---|
| $V_{CC}$ for Retention Data | | $V_{DR}$ | 2 | | | V | |
| Data Retention Current L version | $\overline{CE} \geq V_{CC}$ -0.2V Other inputs: $V_{IN} \geq V_{CC}$ -0.2V or $V_{IN} \leq V_{SS}$+0.2V $V_{CC}$ = 2V | | $I_{CCDR}$ | TBD | 50 | µA | 15 |
| Data Retention Current LP version | $\overline{CE} \geq V_{CC}$ -0.2V $V_{CC}$ = 2V | | $I_{CCDR}$ | TBD | 50 | µA | 15 |
| Chip Deselect to Data Retention Time | | ${}^tCDR$ | 0 | | | ns | 4 |
| Operation Recovery Time | | ${}^tR$ | ${}^tRC$ | | | ns | 4, 11 |

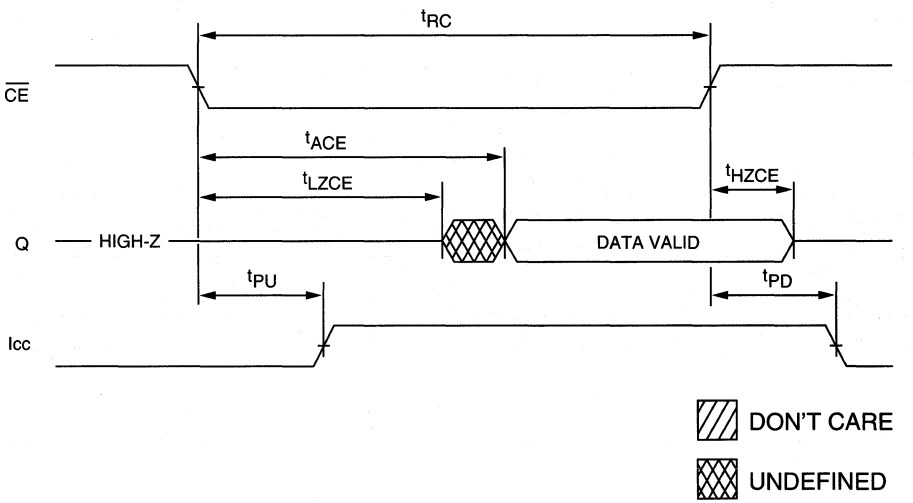
## LOW Vcc DATA RETENTION WAVEFORM



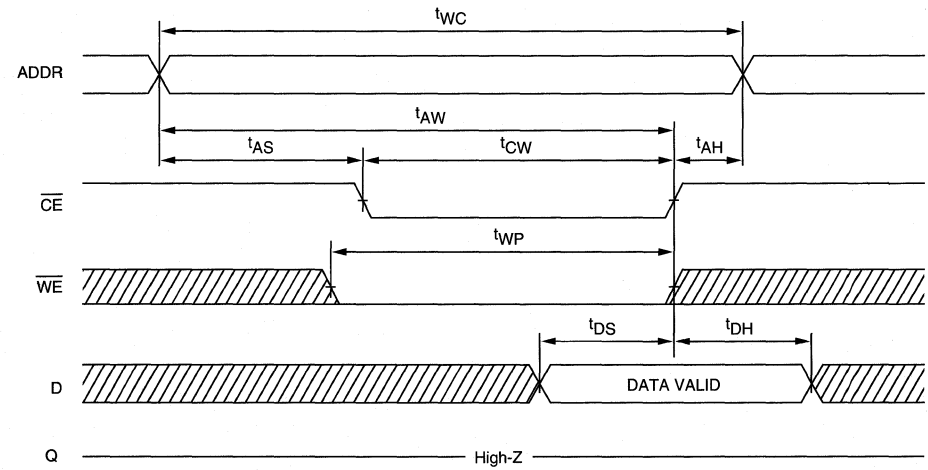

## READ CYCLE NO. 1 [8, 9]




## READ CYCLE NO. 2 [7, 8, 10]



## WRITE CYCLE NO. 1 [12]
(Chip Enable Controlled)




## WRITE CYCLE NO. 2 [7, 12]
(Write Enable Controlled)